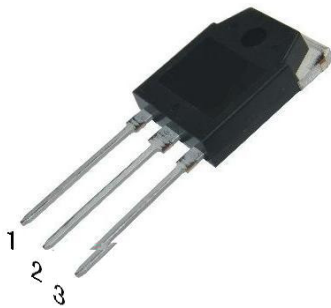
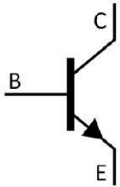


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Silicon NPN transistor in a TO-3P Plastic Package.

High breakdown voltage, high speed, wide SOA.

Horizontal deflection output for TV and CRT monitor.



PIN1 Base PIN 2 Collector PIN 3 Emitter

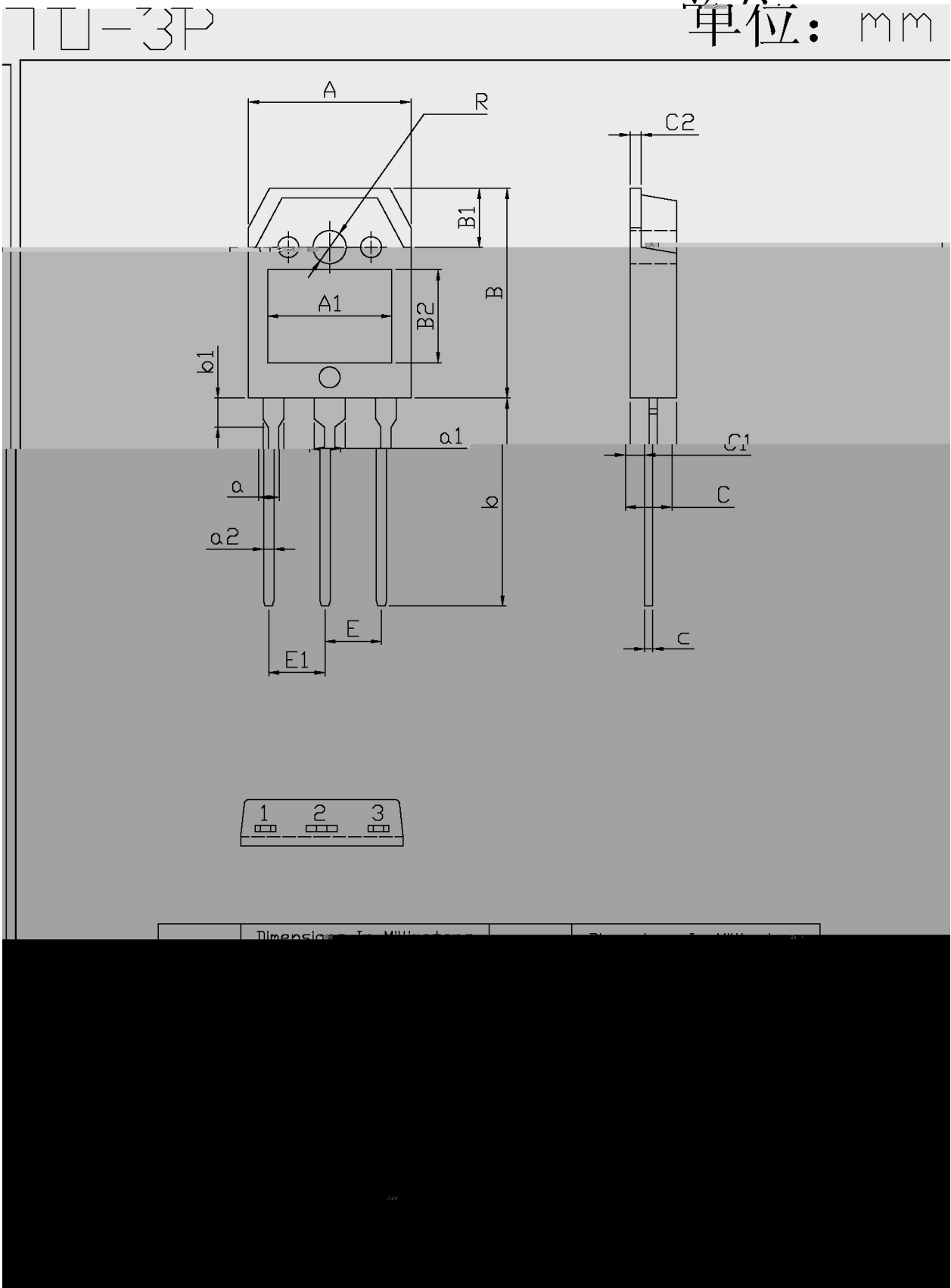
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CES}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	20	A
Peak Collector Current	I_{CP}	30	A
Base Current	P_C	3	W
Collector Power Dissipation	$P_{C(TC=25)}$	200	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

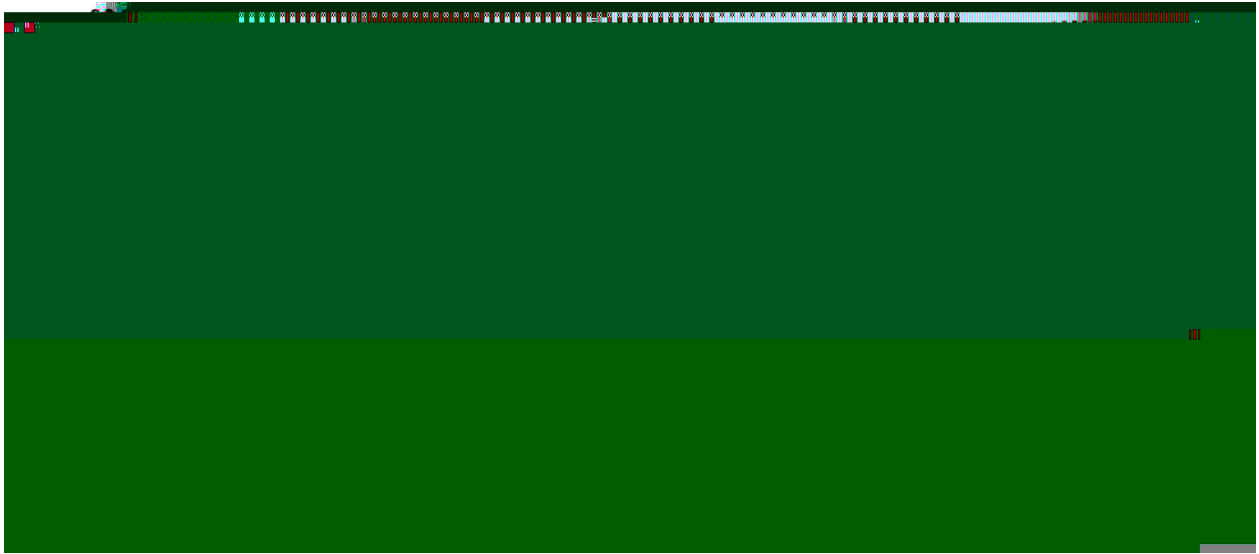
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1mA$ $I_E=0$	1500			V
Collector to Base Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	800			V
Collector to Emitter Breakdown Voltage	V_{EBO}	$I_E=1mA$ $I_C=0$	6			V

Collector Cut-Off Current





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Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-3P	30	15	450	5	2250	497.5×46×8	555×164×50	575×290×180